

Dual isolated high-voltage switching diode 9 June 2015

Product data sheet

1. General description

Dual high-voltage switching diode encapsulated in a very small SOT353 (SC-88A) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High switching speed: $t_{rr} \le 50$ ns
- Low leakage current
- Reverse voltage V_R ≤ 250 V
- Low capacitance: C_d ≤ 2 pF
- Very small SMD plastic package
- AEC-Q101 qualified

3. Applications

- High-speed switching at high voltage
- High-voltage general-purpose switching
- Voltage clamping
- Reverse polarity protection

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	-					,
I _F	forward current	T_j = 25 °C; single diode loaded	-	-	225	mA
V _R	reverse voltage	T _j = 25 °C	-	-	250	V
Per diode						
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	25	100	nA
t _{rr}	reverse recovery time	I_F = 10 mA; I_R = 10 mA; $I_{R(meas)}$ = 1 mA; R _L = 100 Ω; T _j = 25 °C	-	-	50	ns





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode diode 1	54	5 4
2	n.c.	not connected		
3	A2	anode diode 2		
4	K2	cathode diode 2		
5	K1	cathode diode 1	TSSOP5 (SOT353)	1 2 3 aaa-018440

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BAS21PG	TSSOP5	plastic surface-mounted package; 5 leads	SOT353

7. Marking

Table 4. Marking codes	
Type number	Marking code
BAS21PG	PG

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode	L					
V _R	reverse voltage	T _j = 25 °C		-	250	V
l _F	forward current	T_j = 25 °C; single diode loaded		-	225	mA
		T_j = 25 °C; double diode loaded		-	125	mA
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ = 25 %; T _j = 25 °C		-	625	mA
I _{FSM}	non-repetitive peak forward current	t_p = 1 µs; $T_{j(init)}$ = 25 °C; square wave		-	9	А
		t_p = 100 µs; $T_{j(init)}$ = 25 °C; square wave		-	3	А
		t_p = 10 ms; $T_{j(init)}$ = 25 °C; square wave		-	1.7	А
Per device;	one diode loaded	·				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	255	mW
			[2]	-	290	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

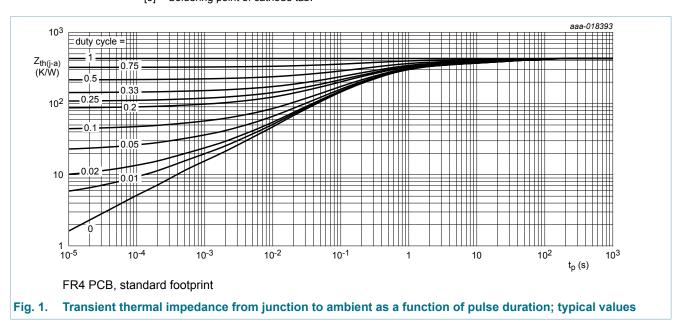
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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	-	495	K/W
			[2]	-	-	430	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[3]	-	-	95	K/W

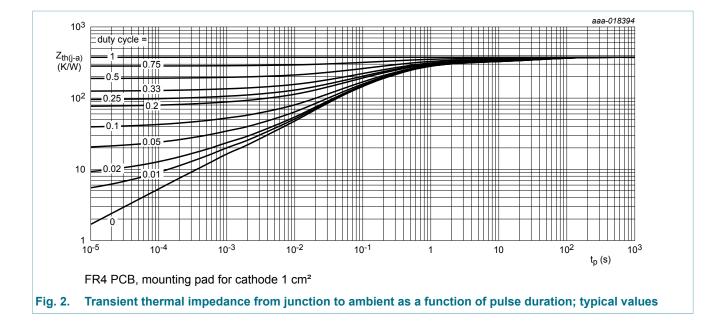
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².



[3] Soldering point of cathode tab.

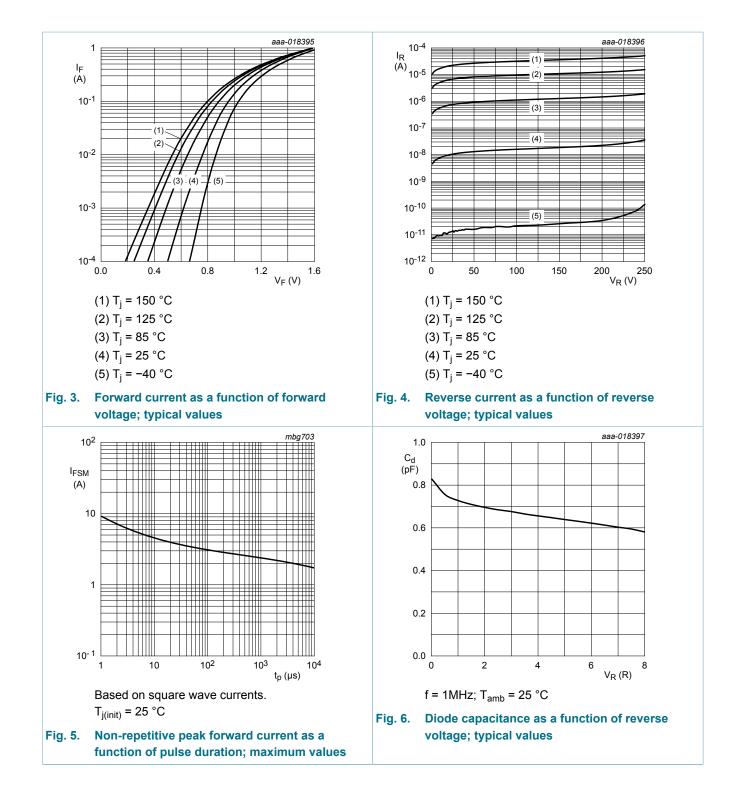
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode		· · · · · · · · · · · · · · · · · · ·	1		1	_
V _{(BR)R}	reverse breakdown voltage	I _R = 100 μA; T _j = 25 °C	250	-	-	V
V _F	forward voltage	I _F = 100 mA; T _j = 25 °C	-	-	1	V
		I _F = 200 mA; T _j = 25 °C	-	-	1.25	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	25	100	nA
		V _R = 200 V; T _j = 150 °C	-	40	-	μA
C _d	diode capacitance	V _R = 0 V; f = 1 MHz; T _j = 25 °C	-	0.8	2	pF
t _{rr}	reverse recovery time	I_F = 10 mA; I_R = 10 mA; $I_{R(meas)}$ = 1 mA; R _L = 100 Ω; T _j = 25 °C	-	-	50	ns

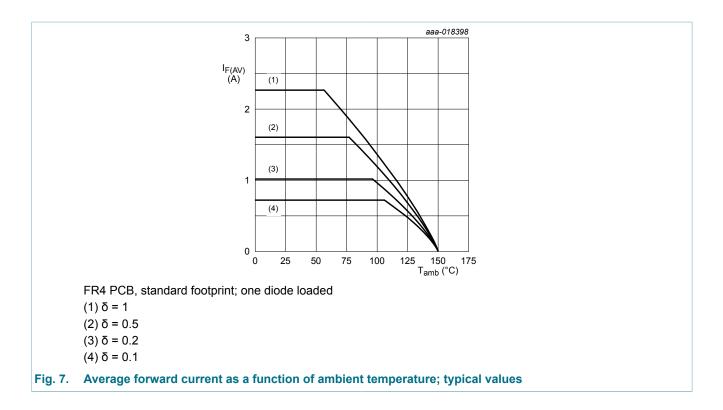
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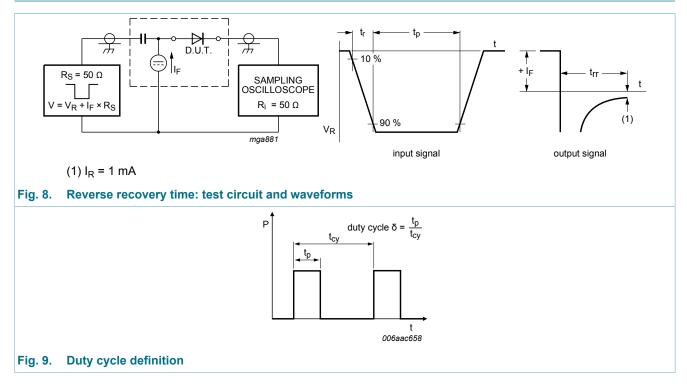
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BAS21PG



11. Test information



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

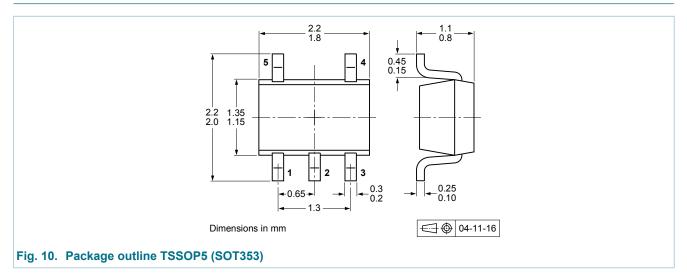
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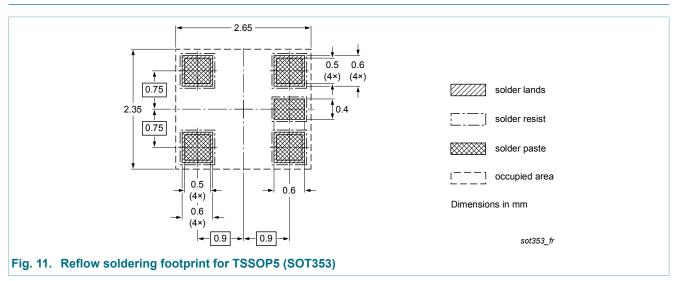
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



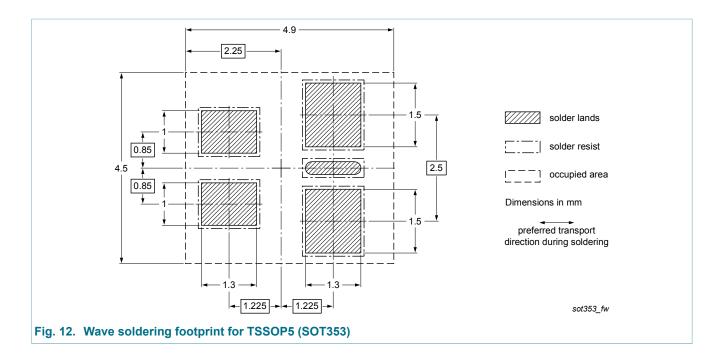
13. Soldering



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BAS21PG

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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BAS21PG v.1	20150609	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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